## **SQM50020EL**



**Vishay Siliconix** 

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0020				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0025				
I <sub>D</sub> (A)	120				
Configuration	Single				



N-Channel MOSFET

### FEATURES

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified
- 100 %  $\rm R_g$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM50020EL-GE3		

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	Ι <sub>D</sub>	120	
	T <sub>C</sub> = 125 °C		120	
Continuous Source Current (Diode Conduct	ion) <sup>a</sup>	I <sub>S</sub>	120	А
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	300	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	75	
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	281	mJ
Mauianum Daura Diasia atian b	T <sub>C</sub> = 25 °C	P <sub>D</sub>	375	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C		125	vv
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	- 0/10		

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					<u> </u>		<b>-</b>	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	60 V		1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	1.5	mA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		$V_{GS} = 10 V$	I <sub>D</sub> = 30 A	-	0.0016	0.0020		
Drain-Source On-State Resistance <sup>a</sup>	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0031	Ω	
Drain-Source On-State Resistance "	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0037		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 20 A	-	0.0020	0.0025		
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	164	-	S	
Dynamic <sup>b</sup>		<u>.</u>					•	
Input Capacitance	C <sub>iss</sub>			-	12 060	15 100	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	5750	7200		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	860	1100		
Total Gate Charge <sup>c</sup>	Qg			-	128	200		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 80 \text{ A}$	-	33	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	11	-		
Gate Resistance	Rg	f = 1 MHz		0.8	1.68	2.6	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{L}} = 0.375 \ \Omega$ $\text{I}_{\text{D}} \cong 80 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \ \Omega$		-	20	25		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	15	40	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	65	100		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	20		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	300	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-	0.88	1.5	V		

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

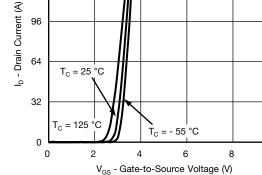
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

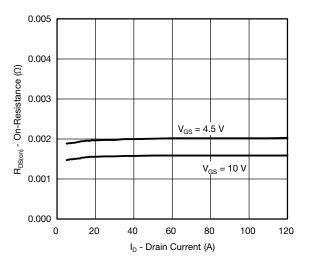
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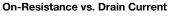
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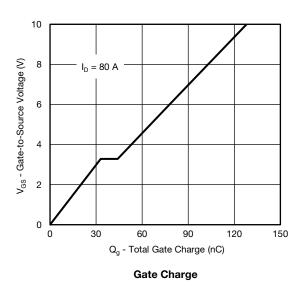
128











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10

20

30

V<sub>DS</sub> - Drain-to-Source Voltage (V)

Capacitance

40

50

60

 $\rm C_{rss}$ 

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10

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**ISHAY** 

200

160

120

80

40

0

300

240

180

120

60

0

18 000

14 400

10 800

7200

3600

0

0

C - Capacitance (pF)

0

10

g<sub>fs</sub> - Transconductance (S)

0

I<sub>D</sub> - Drain Current (A)

V<sub>GS</sub> = 10 V thru 4 V

2

4

 $T_{C} = 25 \ ^{\circ}C$ 

20

Ciss

 $\mathsf{C}_{\mathrm{oss}}$ 

I<sub>D</sub> - Drain Current (A)

Transconductance

**TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

 $V_{GS} = 3 V$ 

8

T<sub>C</sub> = - 55 °C

T<sub>C</sub> = 125 °C

40

50

10

6

30

V<sub>DS</sub> - Drain-to-Source Voltage (V)

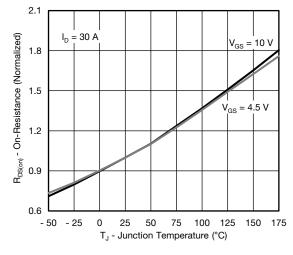
**Output Characteristics** 

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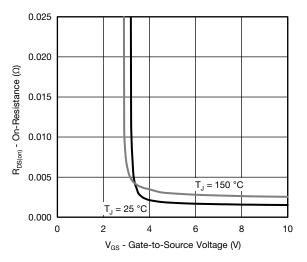


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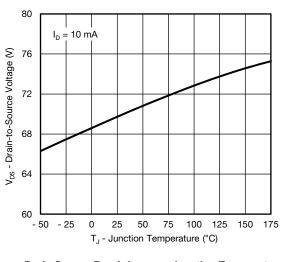
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



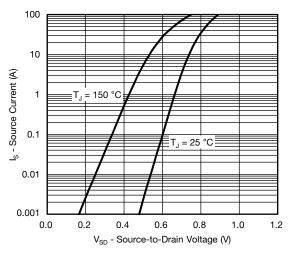
**On-Resistance vs. Junction Temperature** 



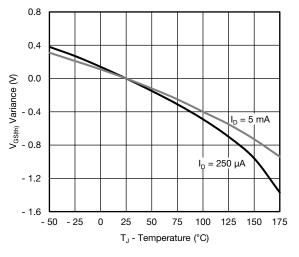
**On-Resistance vs. Gate-to-Source Voltage** 



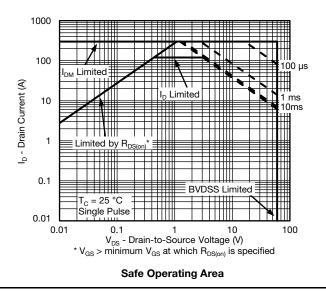
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



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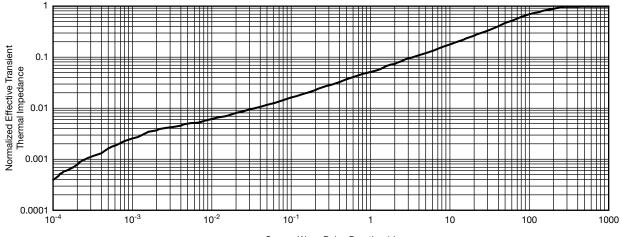
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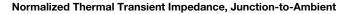


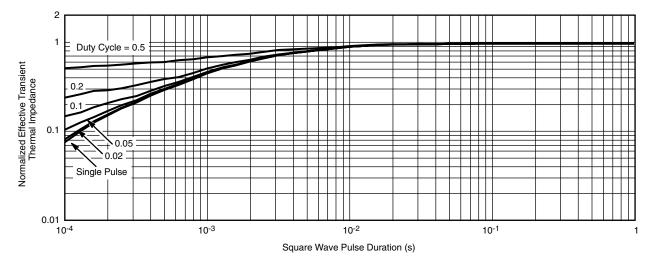
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### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)







#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65377.

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## D<sup>2</sup>PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D<sup>2</sup>PAK / TO-263 and TO-262 packages:

DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE
SQM100N04-2m7	SQM100N04-2M7-GE3	SQM100N04-2M7_GE3
SQM100N10-10	SQM100N10-10-GE3	SQM100N10-10_GE3
SQM110N05-06L	SQM110N05-06L-GE3	SQM110N05-06L_GE3
SQM110P06-8m9L	SQM110P06-8M9L-GE3	SQM110P06-8M9L_GE3
SQM120N02-1m3L	SQM120N02-1M3L-GE3	SQM120N02-1M3L_GE3
SQM120N03-1m5L	SQM120N03-1M5L-GE3	SQM120N03-1M5L_GE3
SQM120N04-1m7	SQM120N04-1M7-GE3	SQM120N04-1M7_GE3
SQM120N04-1m7L	SQM120N04-1M7L-GE3	SQM120N04-1M7L_GE3
SQM120N04-1m9	SQM120N04-1M9-GE3	SQM120N04-1M9_GE3
SQM120N06-06	SQM120N06-06-GE3	SQM120N06-06_GE3
SQM120N06-3m5L	SQM120N06-3M5L-GE3	SQM120N06-3M5L_GE3
SQM120N10-09	SQM120N10-09-GE3	SQM120N10-09_GE3
SQM120N10-3m8	SQM120N10-3M8-GE3	SQM120N10-3M8_GE3
SQM120P04-04L	SQM120P04-04L-GE3	SQM120P04-04L_GE3
SQM120P06-07L	SQM120P06-07L-GE3	SQM120P06-07L_GE3
SQM120P10-10m1L	-	SQM120P10_10m1LGE3
SQM200N04-1m1L	SQM200N04-1M1L-GE3	SQM200N04-1M1L_GE3
SQM200N04-1m7L	SQM200N04-1M7L-GE3	SQM200N04-1M7L_GE3
SQM200N04-1m8	SQM200N04-1M8-GE3	SQM200N04-1M8_GE3
SQM25N15-52	SQM25N15-52-GE3	SQM25N15-52_GE3
SQM35N30-97	SQM35N30-97-GE3	SQM35N30-97_GE3
SQM40010EL	-	SQM40010EL_GE3
SQM40N10-30	SQM40N10-30-GE3	SQM40N10-30_GE3
SQM40N15-38	SQM40N15-38-GE3	SQM40N15-38_GE3
SQM40P10-40L	SQM40P10-40L-GE3	SQM40P10-40L_GE3
SQM47N10-24L	SQM47N10-24L-GE3	SQM47N10-24L_GE3
SQM50020EL	-	SQM50020EL_GE3
SQM50N04-4m0L	SQM50N04-4M0L-GE3	SQM50N04-4M0L_GE3
SQM50N04-4m1	SQM50N04-4M1-GE3	SQM50N04-4M1_GE3
SQM50P03-07	SQM50P03-07-GE3	SQM50P03-07_GE3
SQM50P04-09L	SQM50P04-09L-GE3	SQM50P04-09L_GE3
SQM50P06-15L	SQM50P06-15L-GE3	SQM50P06-15L_GE3
SQM50P08-25L	SQM50P08-25L-GE3	SQM50P08-25L_GE3
SQM60030E	-	SQM60030E_GE3
SQM60N06-15	SQM60N06-15-GE3	SQM60N06-15_GE3
SQM60N20-35	SQM60N20-35-GE3	SQM60N20-35_GE3
SQM70060EL	-	SQM70060EL_GE3
SQM85N15-19	SQM85N15-19-GE3	SQM85N15-19_GE3
SQV120N10-3m8	SQV120N10-3m8-GE3	SQV120N10-3m8_GE3
SQV120N06-4m7L	_	SQV120N06-4m7L_GE3

#### Note

a. Old ordering code is obsolete and no longer valid for new orders



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TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
	А	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М		0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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